

L Number	Hits	Search Text	DB	Time stamp
-	2	("6215595").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:37
-	64	{"3667832"   "4733944"   "4943733"   "5097291"   "5263250"   "5414559"   "5561081"   "5657138"   "5721416"   "5756364"   "5815494"   "5854803"   "5858822"   "5893990"   "5897799"   "5900980"   "5907770"   "5923966"   "5959779"   "6104535"   "6137633").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 13:47
-	14653	excimer adj laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:33
-	2078666	beam near\$4 (homogeneity or homogeneous or homogenizer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 13:53
-	9238	(excimer adj laser) and (beam near\$4 (homogeneity or homogeneous or homogenizer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 13:53
-	33846	((thin adj film adj transistor) or (tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 13:55
-	848	((excimer adj laser) and (beam near\$4 (homogeneity or homogeneous or homogenizer))) and (((thin adj film adj transistor) or (tft)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 13:55
-	118	pulsed adj laser and (((excimer adj laser) and (beam near\$4 (homogeneity or homogeneous or homogenizer))) and (((thin adj film adj transistor) or (tft))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:15
-	282	(438/149).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:32
-	103	laser and (("438/149").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:35
-	79	pulsed adj laser and (((excimer adj laser) and (beam near\$4 (homogeneity or homogeneous or homogenizer))) and (((thin adj film adj transistor) or (tft)))) and glass adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:39
-	49	(438/150).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:39
-	377	(438/151).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:40

-	161	(438/152).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:40
-	105	(438/153).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:41
-	479	(438/164).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 14:42
-	53	glass adj substrate and laser and (("438/164").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 15:41
-	3	("5858473").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/26 15:42
-	1274	ion adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 12:44
-	56160	glass adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 12:44
-	544	(ion adj doping) and (glass adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 12:45
-	19765	tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 12:45
-	458	((ion adj doping) and (glass adj substrate)) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 12:45
-	1274	ion adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:14
-	290	pulsed adj excimer adj laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:15
-	1	"US 6215595 B1".DID. and ("US 6215595 B1".DID. and ("6215595").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:15
-	875	(homogeneity or homogeneous or homogenizer) and ((thin adj film adj transistor) or tft)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:17

-	0	(ion adj doping) and (pulsed adj excimer adj laser) and ("US 6215595 B1".DID. and ("US 6215595 B1".DID. and ("6215595").PN.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:17
-	6	(ion adj doping) and (pulsed adj excimer adj laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:21
-	1	(pulsed adj excimer adj laser) and ((ion adj doping) and ((homogeneity or homogeneous or homogenizer) and ((thin adj film adj transistor) or tft)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:21
-	54	(ion adj doping) and ((homogeneity or homogeneous or homogenizer) and ((thin adj film adj transistor) or tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:25
-	1	(ion adj doping) and (pulsed adj excimer adj laser) and ((homogeneity or homogeneous or homogenizer) and ((thin adj film adj transistor) or tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 13:26
-	2	("5958800").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 16:16
-	24480	silicon and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 18:28
-	1274	ion adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 18:28
-	109	(silicon and germanium) and (ion adj doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 18:28
-	3	("5180690").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/27 19:09
-	661	"piii" or plasma adj immersion adj ion adj implantation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:24
-	577793	laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:25
-	110	("piii" or plasma adj immersion adj ion adj implantation) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:29
-	835	glass adj substrate and ion adj doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:30

-	737	laser and (glass adj substrate and ion adj doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:31
-	1150067	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:34
-	712	(laser and (glass adj substrate and ion adj doping)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 16:57
-	214	(laser and (glass adj substrate and ion adj doping)) and semiconductor and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 17:01
-	162	(laser and (glass adj substrate and ion adj doping)) and semiconductor and cmos and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 17:06
-	448	(laser and (glass adj substrate and ion adj doping)) and semiconductor and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 17:09
-	11	((("5699191") or ("5986807") or ("6061375") or ("6212012") or ("6300176"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 18:40
-	9568	moving near substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:24
-	161	laser adj annealing and (moving near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:25
-	135	glass adj substrate and (laser adj annealing and (moving near substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 15:08
-	321	laser and divergence and convergence and (inspection or monitoring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 15:09
-	58	substrate and defects and surface and (laser and divergence and convergence and (inspection or monitoring))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 15:13
-	52	(annular or circle or circular or round) and (substrate and defects and surface and (laser and divergence and convergence and (inspection or monitoring)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 15:14
-	585	(438/164).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:58

-	644	(438/166).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/03 15:58
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